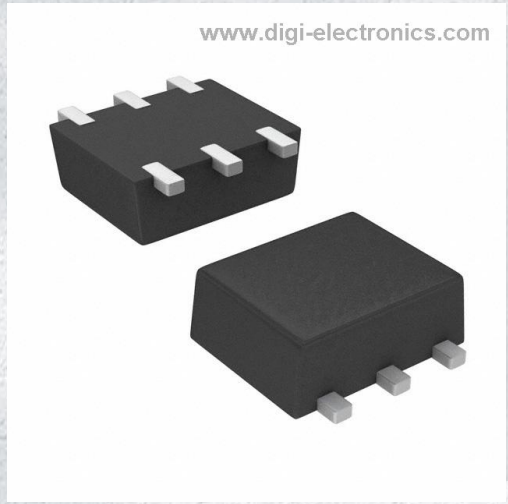
SI1050X-T1-GE3 Datasheet



DiGi Electronics Part Number	SI1050X-T1-GE3-DG
Manufacturer	Vishay Siliconix
Manufacturer Product Number	SI1050X-T1-GE3
Description	MOSFET N-CH 8V 1.34A SC89-6
Detailed Description	N-Channel 8 V 1.34A (Ta) 236mW (Ta) Surface Mount SC-89 (SOT-563F)

https://www.DiGi-Electronics.com

Tel: +00 852-30501935

RFQ Email: Info@DiGi-Electronics.com

Purchase and inquiry

Manufacturer Product Number:	Manufacturer:
SI1050X-T1-GE3	Vishay Siliconix
Series:	Product Status:
TrenchFET®	Active
FET Type:	Technology:
N-Channel	MOSFET (Metal Oxide)
Drain to Source Voltage (Vdss):	Current - Continuous Drain (Id) @ 25°C:
8 V	1.34A (Ta)
Drive Voltage (Max Rds On, Min Rds On):	Rds On (Max) @ Id, Vgs:
1.5V, 4.5V	86mOhm @ 1.34A, 4.5V
Vgs(th) (Max) @ Id:	Gate Charge (Qg) (Max) @ Vgs:
900mV @ 250µA	11.6 nC @ 5 V
Vgs (Max):	Input Capacitance (Ciss) (Max) @ Vds:
±5V	585 pF @ 4 V
FET Feature:	Power Dissipation (Max):
-	236mW (Ta)
Operating Temperature:	Mounting Type:
-55°C ~ 150°C (TJ)	Surface Mount
Supplier Device Package:	Package / Case:
SC-89 (SOT-563F)	SOT-563, SOT-666
Base Product Number:	
SI1050	

Environmental & Export classification

RoHS Status:	Moisture Sensitivity Level (MSL):
ROHS3 Compliant	1 (Unlimited)
REACH Status:	ECCN:
REACH Unaffected	EAR99
HTSUS:	
8541.21.0095	

N-Channel 8 V (D-S) MOSFET

PRODUCT SUMMARY			
V_{DS} (V)	$R_{DS(on)}$ (Ω)	I_D (A)	Q_g (Typ.)
8	0.086 at V_{GS} = 4.5 V	1.34[a]	7.1
	0.093 at V_{GS} = 2.5 V	1.29	
	0.102 at V_{GS} = 1.8 V	1.23	
	0.120 at V_{GS} = 1.5 V	0.7	

FEATURES

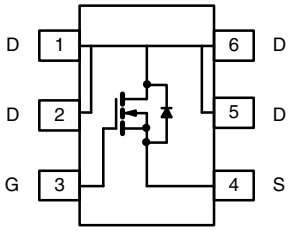
- **Halogen-free According to IEC 61249-2-21 Definition**
- TrenchFET® Power MOSFET
- 100 % R_g Tested
- Compliant to RoHS Directive 2002/95/EC

Pb-free
RoHS COMPLIANT
HALOGEN FREE

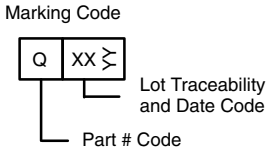
APPLICATIONS

- Load Switch for Portable Devices

SC-89 (6-LEADS)



Top View



Ordering Information: Si1050X-T1-GE3 (Lead (Pb)-free and Halogen-free)

ABSOLUTE MAXIMUM RATINGS (T_A = 25 °C, unless otherwise noted)				
Parameter		**Symbol**	**Limit**	**Unit**
Drain-Source Voltage		V_{DS}	8	V
Gate-Source Voltage		V_{GS}	± 5	
Continuous Drain Current (T_J = 150 °C)[a]	T_A = 25 °C	I_D	1.34[b, c]	A
	T_A = 70 °C		1.07[b, c]	
Pulsed Drain Current		I_{DM}	6	
Continuous Source-Drain Diode Current	T_A = 25 °C	I_S	0.2[b, c]	
Maximum Power Dissipation[a]	T_A = 25 °C	P_D	0.236[b, c]	W
	T_A = 70 °C		0.151[b, c]	
Operating Junction and Storage Temperature Range		T_J, T_{stg}	- 55 to 150	°C

THERMAL RESISTANCE RATINGS					
Parameter		**Symbol**	**Typical**	**Maximum**	**Unit**
Maximum Junction-to-Ambient[b, d]	t ≤ 5 s	R_{thJA}	440	530	°C/W
	Steady State		540	650	

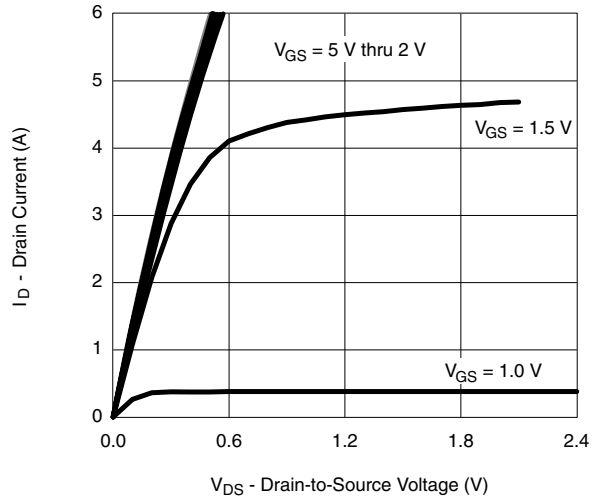
Notes:
a. Based on T_C = 25 °C.
b. Surface mounted on 1" x 1" FR4 board.
c. t = 5 s.
d. Maximum under steady state conditions is 650 °C/W.

SPECIFICATIONS (T_J = 25 °C, unless otherwise noted)						
Parameter	**Symbol**	**Test Conditions**	**Min.**	**Typ.**	**Max.**	**Unit**
Static						
Drain-Source Breakdown Voltage	V_{DS}	V_{GS} = 0 V, I_D = 250 µA	8			V
V_{DS} Temperature Coefficient	$\Delta V_{DS}/T_J$	I_D = 250 µA		18.2		mV/°C
$V_{GS(th)}$ Temperature Coefficient	$\Delta V_{GS(th)}/T_J$			- 2.55		
Gate-Source Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 250 µA	0.35		0.9	V
Gate-Source Leakage	I_{GSS}	V_{DS} = 0 V, V_{GS} = ± 5 V			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = 8 V, V_{GS} = 0 V			1	µA
		V_{DS} = 8 V, V_{GS} = 0 V, T_J = 85 °C			10	
On-State Drain Current[a]	$I_{D(on)}$	V_{DS} = ≥ 5 V, V_{GS} = 4.5 V	6			A
Drain-Source On-State Resistance[a]	$R_{DS(on)}$	V_{GS} = 4.5 V, I_D = 1.34 A		0.071	0.086	Ω
		V_{GS} = 2.5 V, I_D = 1.29 A		0.078	0.093	
		V_{GS} = 1.8 V, I_D = 1.23 A		0.085	0.102	
		V_{GS} = 1.5 V, I_D = 0.76 A		0.092	0.120	
Forward Transconductance	g_{fs}	V_{DS} = 4 V, I_D = 1.34 A		4.12		S
Dynamic[b]						
Input Capacitance	C_{iss}	V_{DS} = 4 V, V_{GS} = 0 V, f = 1 MHz		585		pF
Output Capacitance	C_{oss}			190		
Reverse Transfer Capacitance	C_{rss}			130		
Total Gate Charge	Q_g	V_{DS} = 4 V, V_{GS} = 5 V, I_D = 1.34 A		7.7	11.6	nC
		V_{DS} = 4 V, V_{GS} = 4.5 V, I_D = 1.34 A		7.1	10.7	
Gate-Source Charge	Q_{gs}			1.14		
Gate-Drain Charge	Q_{gd}			1.69		
Gate Resistance	R_g	f = 1 MHz		3.5	4.6	Ω
Turn-On Delay Time	$t_{d(on)}$	V_{DD} = 4 V, R_L = 3.6 Ω I_D ≅ 1.1 A, V_{GEN} = 4.5 V, R_g = 1 Ω		6.8	10.2	ns
Rise Time	t_r			35	53	
Turn-Off DelayTime	$t_{d(off)}$			25	37.5	
Fall Time	t_f			6	9	
Drain-Source Body Diode Characteristics						
Pulse Diode Forward Current[a]	I_{SM}				6	A
Body Diode Voltage	V_{SD}	I_S = 1.0 A		0.8	1.2	V
Body Diode Reverse Recovery Time	t_{rr}	I_F = 1.0 A, dI/dt = 100 A/µs		18.5	28	nC
Body Diode Reverse Recovery Charge	Q_{rr}			3.7	5.7	ns
Reverse Recovery Fall Time	t_a			6.7		
Reverse Recovery Rise Time	t_b			11.8		

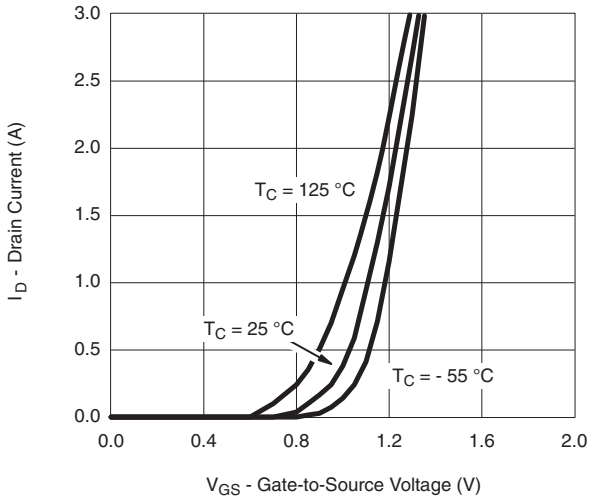
Notes:
a. Pulse test; pulse width ≤ 300 µs, duty cycle ≤ 2 %.
b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

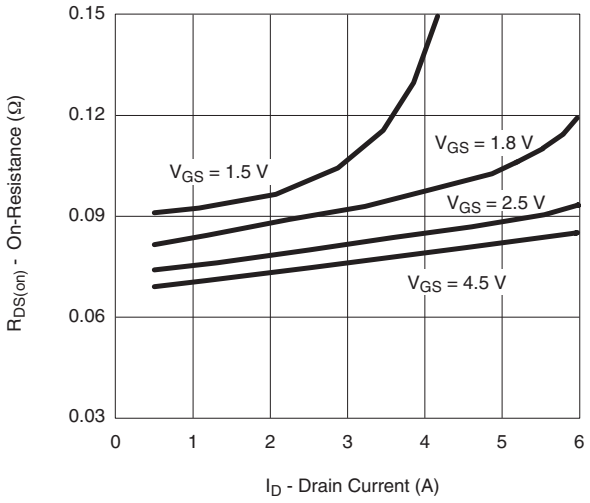
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



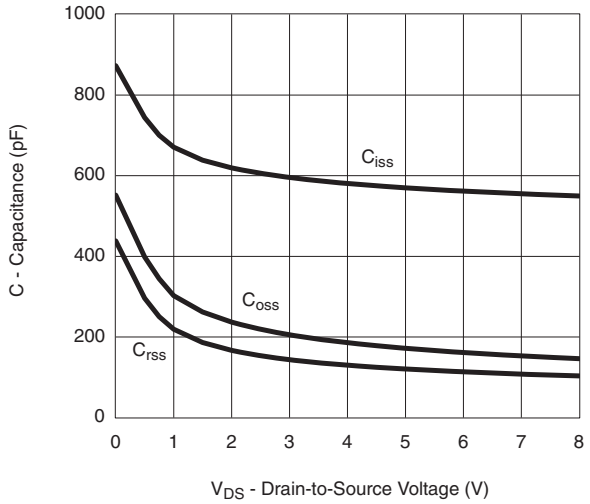
Output Characteristics



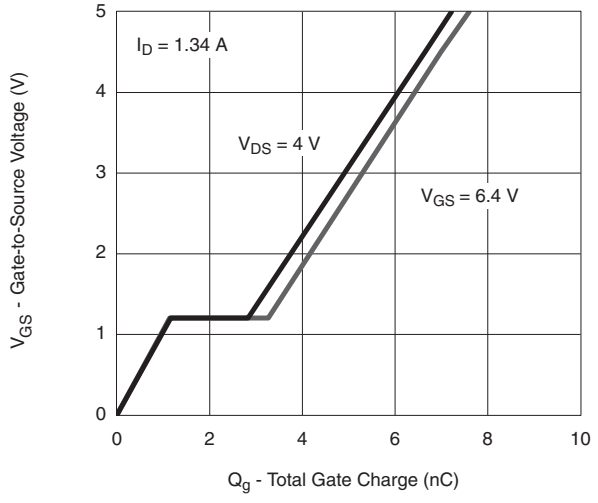
Transfer Characteristics curves vs. Temp.



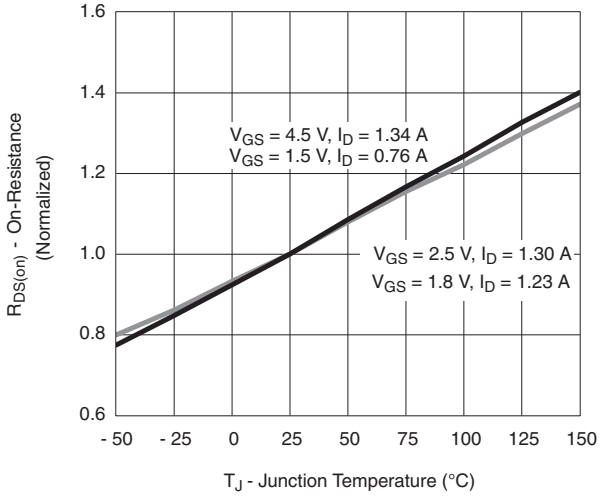
On-Resistance vs. Drain Current



Capacitance

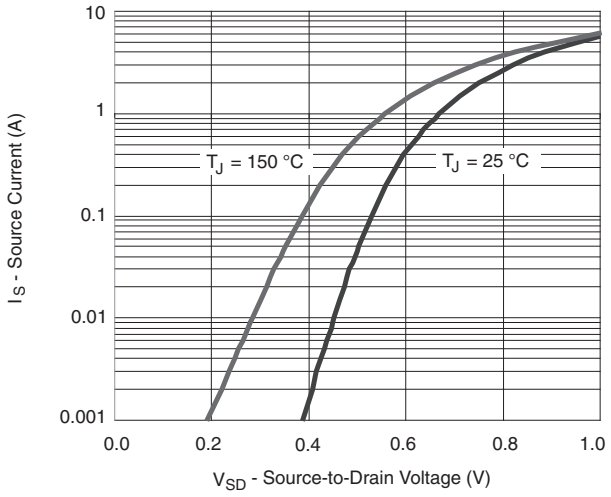


Q_g - Gate Charge

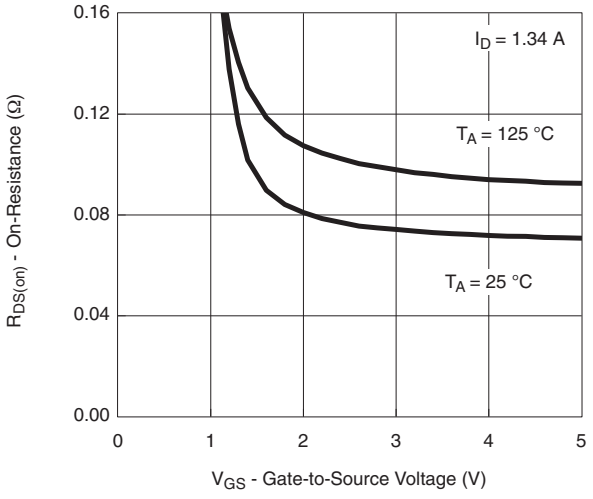


On-Resistance vs. Junction Temperature

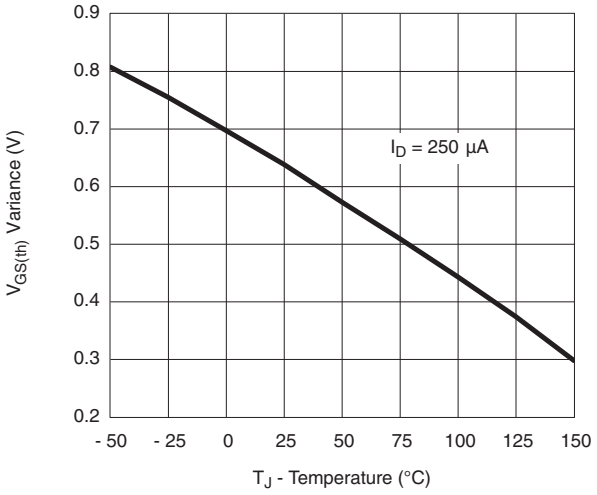
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



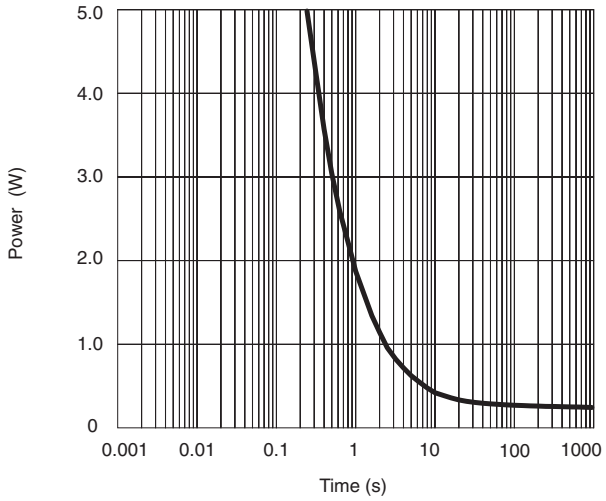
Source-Drain Diode Forward Voltage



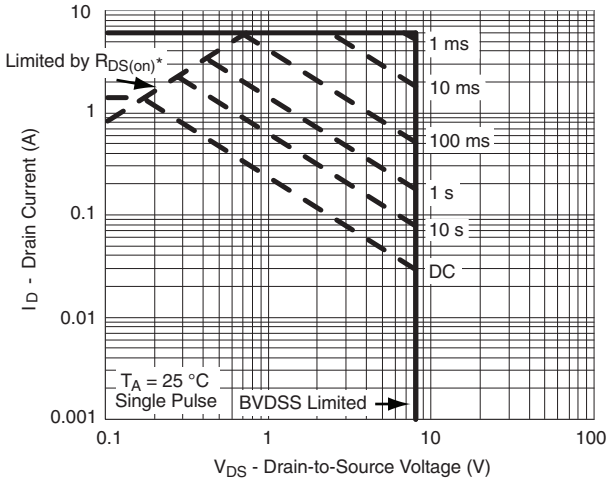
$R_{DS(on)}$ vs V_{GS} vs Temperature



Threshold Voltage



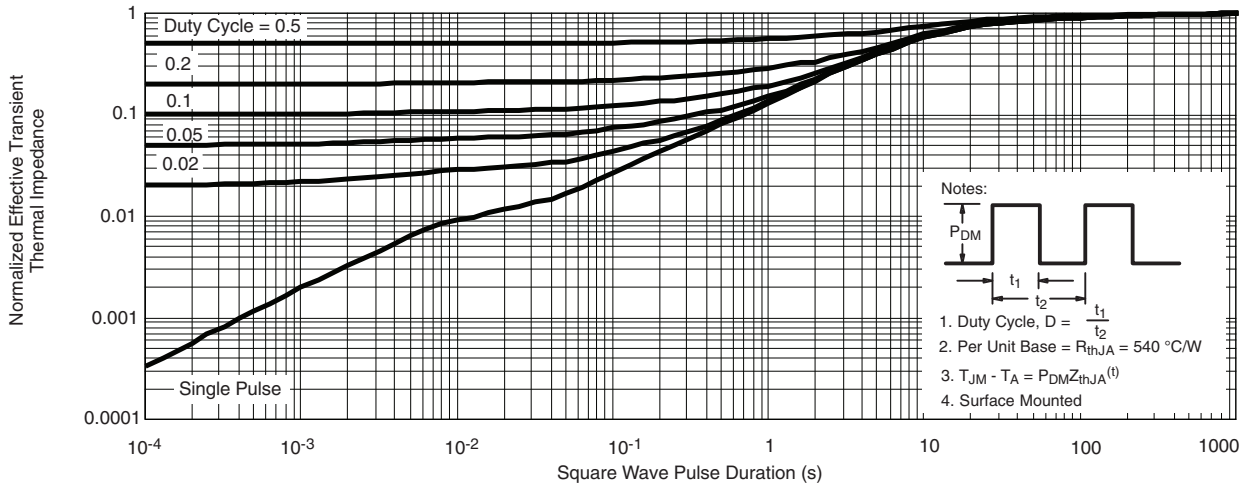
Single Pulse Power



* V_{GS} > minimum V_{GS} at which $R_{DS(on)}$ is specified

Safe Operating Area, Junction-to-Ambient

TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?73896.

VISHAY

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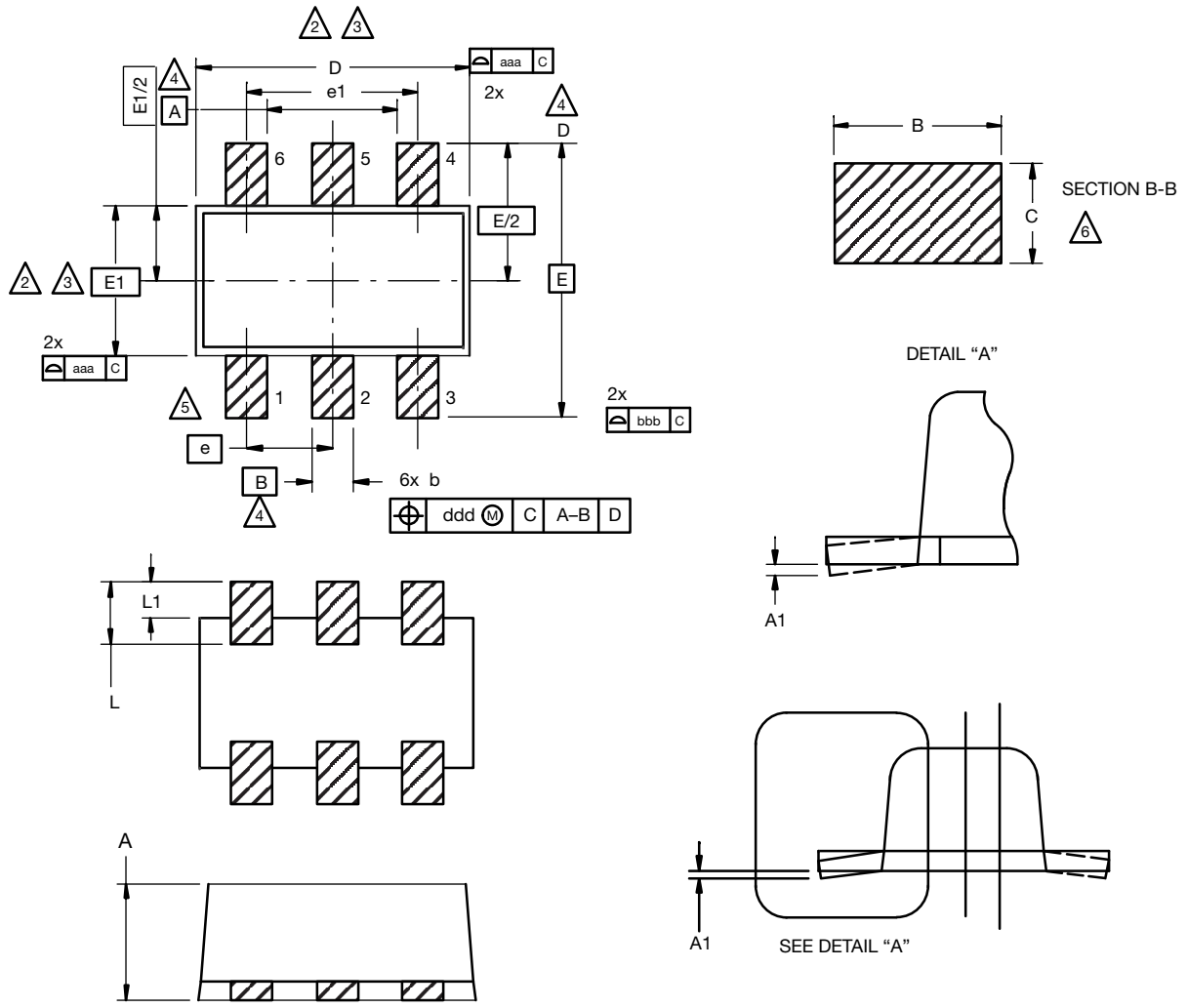
Package Information

Vishay Siliconix

SC-89 6-Leads (SOT-563F)



Notes

1. Dimensions in millimeters.

2. Dimension D does not include mold flash, protrusions or gate burrs. Mold flush, protrusions or gate burrs shall not exceed 0.15 mm per dimension E1 does not include interlead flash or protrusion, interlead flash or protrusion shall not exceed 0.15 mm per side.

3. Dimensions D and E1 are determined at the outmost extremes of the plastic body exclusive of mold flash, the bar burrs, gate burrs and interlead flash, but including any mismatch between the top and the bottom of the plastic body.

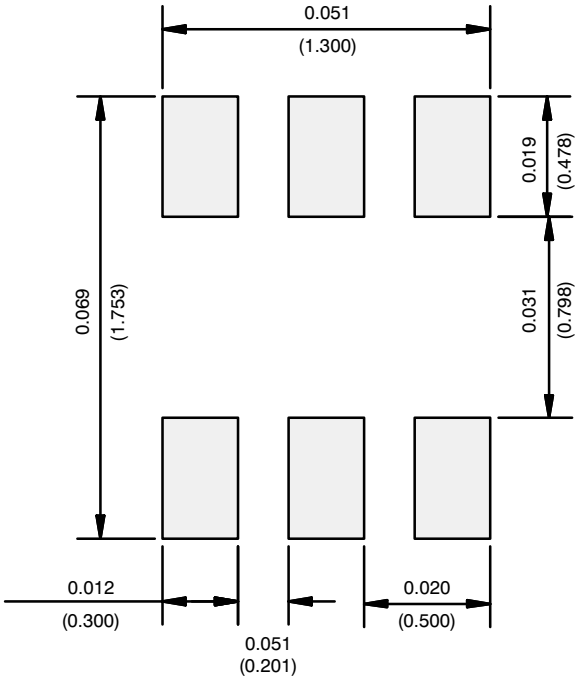
4. Datums A, B and D to be determined 0.10 mm from the lead tip.

5. Terminal numbers are shown for reference only.

6. These dimensions apply to the flat section of the lead between 0.08 mm and 0.15 mm from the lead tip.

DIM.	MILLIMETERS		
	MIN.	NOM.	MAX.
A	0.56	0.58	0.60
A1	0	0.02	0.10
b	0.15	0.22	0.30
c	0.10	0.14	0.18
D	1.50	1.60	1.70
E	1.50	1.60	1.70
E1	1.15	1.20	1.25
e	0.45	0.50	0.55
e1	0.95	1.00	1.05
L	0.25	0.35	0.50
L1	0.10	0.20	0.30
C14-0439-Rev. C, 11-Aug-14 DWG: 5880			

RECOMMENDED MINIMUM PADS FOR SC-89: 6-Lead



Recommended Minimum Pads
Dimensions in Inches/(mm)

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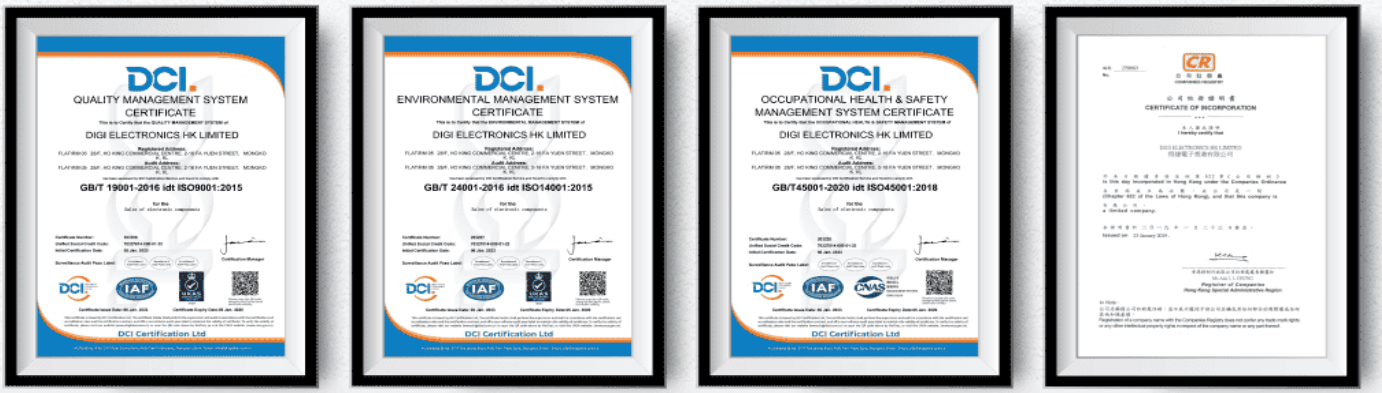

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